

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A semiconductor device having only one wiring layer including a plurality of wirings juxtaposed with one another and a first SiOF insulating film being in contact with the wirings, characterized in that the fluorine concentration of the first SiOF insulating film at a wiring gap portion is set to be higher than the fluorine concentration of ~~the~~ a second SiOF insulating film on the upper side of the wirings, wherein the first SiOF insulating film is in contact with the wirings only at the wiring gap portion and is not in contact with the upper side of the wirings.

2. (Canceled)

3. (Previously Amended) The semiconductor device as claimed in claim 1, wherein the thickness of the first SiOF film at a center of the wiring gap portion is within the range of 1/3 to 1/1 times of the thickness of the wirings.

4. (Original) The semiconductor device as claimed in claim 1, wherein the fluorine concentration of the first SiOF film is set to 5 atom % or more, and the fluorine concentration of the second SiOF film is set to be less than 5 atom %.

5. (Currently Amended) A semiconductor device having a plurality of wiring layers each having a plurality of wirings juxtaposed with one another and a first SiOF interlayer insulating film, characterized in that the fluorine concentration of the first SiOF interlayer insulating film at a wiring gap portion is set to be higher than the fluorine concentration of ~~the~~ a second SiOF interlayer insulating film on the upper side of the wirings, wherein the first SiOF interlayer insulating film is in contact with the wirings only at the wiring gap portion and is not in contact with the upper side of the wirings.

6. (Canceled)

7. (Previously Amended) The semiconductor device as claimed in claim 5, wherein the thickness of the first SiOF film at a center of the wiring gap portion is within the range of $1/3$ to $1/1$ times of the thickness of the wirings.

8. (Currently Amended) The semiconductor device as claimed in claim 5 6, wherein the fluorine concentration of the first SiOF film is set to 5 atom % or more, and the fluorine concentration of the second SiOF film is set to be less than 5 atom %.

Claims 9-14 (canceled).